

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A nitride semiconductor laser element comprising: a semiconductor stacked structure including a semiconductor layer of a first conductivity type, an active layer and a semiconductor layer of a second conductivity type, which are stacked one upon the other and each comprises a nitride; a striped waveguide region for a laser light provided on the semiconductor layer of the second conductivity type; and an insulative region for reducing the capacitance of the element, wherein a pn-junction of the semiconductor layer at a peripheral region remote from the waveguide region is broken, the insulative region being present remote from at least a portion of an external edge of the semiconductor stacked structure when viewed in plan, said external edge being remote from the striped waveguide region.

2. (Currently Amended) A nitride semiconductor laser element comprising: a semiconductor stacked structure including a semiconductor layer of a first conductivity type, an active layer and semiconductor layers of a second conductivity type, which are stacked one upon the other and each comprises a nitride; a striped waveguide region for a laser light provided on the semiconductor layer of the second conductivity type; and an insulative region for reducing the capacitance of the element having no depletion layer in the semiconductor layer at a peripheral region remote from the waveguide region, the insulative region being present remote from at least a portion of an external edge of the semiconductor stacked structure when viewed in plan, said external edge being remote from the striped waveguide region.

3. (Previously Presented) The nitride semiconductor laser element according to claim 1, wherein the insulative region for reducing the capacitance of the element is a region formed by implanting ions from the surface of the semiconductor layer of the second conductivity type.

4. (Currently Amended) A nitride semiconductor laser element comprising: a substrate; a semiconductor stacked structure including a semiconductor layer of a first conductivity type, an active layer and a semiconductor layer of a second conductivity type, which are stacked on a main surface of the substrate and each comprises a nitride; a striped waveguide region for a laser light provided on the semiconductor layer of the second conductivity type; an embedded insulation film covering a side face of the waveguide region and a surface of the semiconductor layer of the second conductivity type; a first electrode in contact with a surface of the waveguide region; a protective insulation film covering at least a part of the embedded insulation film; a second electrode substantially connected to the semiconductor layer of the first conductivity type; and an insulative region for reducing the capacitance of the element, provided by converting at least a part of the semiconductor layer at a peripheral region remote from the waveguide region into a higher resistance one by ion implantation, the insulative region being present inwardly remote from at least a portion of an external edge of the semiconductor stacked structure when viewed in plan, said external edge being remote from the striped waveguide region.

5. (Previously Presented) The nitride semiconductor laser element according to claim 1, wherein the insulative region for reducing the capacitance of the element has an impurity peak concentration in the range from 1×10^{18} to 5×10^{21} atoms/cm³.

6. (Previously Presented) The nitride semiconductor laser element according to claim 1, wherein the insulative region for reducing the capacitance of the element has a peak of distribution of the impurity concentration in the depth direction in the range from 200 nm to 1 μ m from the surface of the semiconductor layer of the second conductivity type.

7. (Previously Presented) The nitride semiconductor laser element according to claim 4, wherein the first electrode is formed in contact with the surface of the waveguide region so as to cover a part of the embedded insulation film, a pad electrode is formed in contact with the first electrode so as to cover a part of the protective insulation film, and the insulative region for reducing the capacitance of the element includes a region below the embedded insulation film.

8. (Previously Presented) The nitride semiconductor laser element according to claim 4, wherein the first electrode is formed in contact with the surface of the waveguide region so as to cover a part of the embedded insulation film, a pad electrode is formed in contact with the first electrode so as to cover a part of the protective insulation film, and the insulative region for reducing the capacitance of the element includes a region below the first electrode or the pad electrode.

9. (Previously Presented) The nitride semiconductor laser element according to claim 1, wherein the semiconductor laser element is a laser element for emitting bluish-purple light, and has responsiveness to input of pulse drive current of 1 ns or less.

Claim 10 (Canceled).

11. (Currently Amended) A nitride semiconductor laser element comprising: a semiconductor layer of a first conductivity type, an active layer and a semiconductor layer of a second conductivity type being different from the first conductivity type, which are stacked on a main surface of a substrate and each comprises a nitride; and a striped waveguide region for a laser light provided on the semiconductor layer of the second conductivity type, wherein at least a part of the semiconductor layer of the second conductivity type serves as a region for reducing the capacitance of the element by being converted into the first conductivity type in a direction of thickness at a peripheral region remote from the waveguide region, the region for reducing the capacitance of the element being present remote from at least a portion of an external edge of the semiconductor stacked structure when viewed in plan, said external edge being remote from the striped waveguide region.

12. (Original) The nitride semiconductor laser element according to claim 11, having an npn structure in the peripheral region remote from the waveguide region, wherein the semiconductor layer of the first conductivity type is an n-type semiconductor layer, and the semiconductor layer of the second conductivity type is a p-type semiconductor layer.

13. (Original) The nitride semiconductor laser element according to claim 11, having a pnpn structure in the peripheral region remote from the waveguide region, wherein the semiconductor layer of the first conductivity type is an n-type semiconductor layer, and the semiconductor layer of the second conductivity type is a p-type semiconductor layer.

14. (Currently Amended) A bluish-purple light emitting laser element comprising: a semiconductor layer of a first conductivity type, an active layer and a semiconductor layer of a second conductivity type, which are stacked one upon the other and each comprises a nitride; and a striped waveguide region of a laser light provided on the semiconductor layer of the second conductivity type, wherein the element comprises an insulation region for reducing the capacitance of the element in a peripheral region remote from the waveguide region, the insulation region being present remote from at least a portion of an external edge of the semiconductor stacked structure when viewed in plan, said external edge being remote from the striped waveguide region and wherein responsiveness of the element with respect to input of a pulse drive current is 1 ns or less.

15. (Previously Presented) The nitride semiconductor laser element according to claim 4, wherein the first electrode is formed in contact with the surface of the waveguide region so as to cover a part of the embedded insulation film, and the insulative region for reducing the capacitance of the element includes a region below the first electrode.

16. (Previously Presented) The nitride semiconductor laser element according to claim 4, wherein the insulative region for reducing the capacitance of the element is present remote from a resonance surface of the semiconductor element.

17. (Previously Presented) The nitride semiconductor element according to claim 1, wherein the semiconductor stacked structure is rectangular when viewed in plan.

18. (Previously Presented) The nitride semiconductor element according to claim 2, wherein the semiconductor stacked structure is rectangular when viewed in plan.

19. (Previously Presented) The nitride semiconductor element according to claim 4, wherein the semiconductor stacked structure is rectangular when viewed in plan.

20. (Previously Presented) The nitride semiconductor element according to claim 11, wherein the semiconductor stacked structure is rectangular when viewed in plan.

21. (Previously Presented) The nitride semiconductor element according to claim 14, wherein the semiconductor stacked structure is rectangular when viewed in plan.